

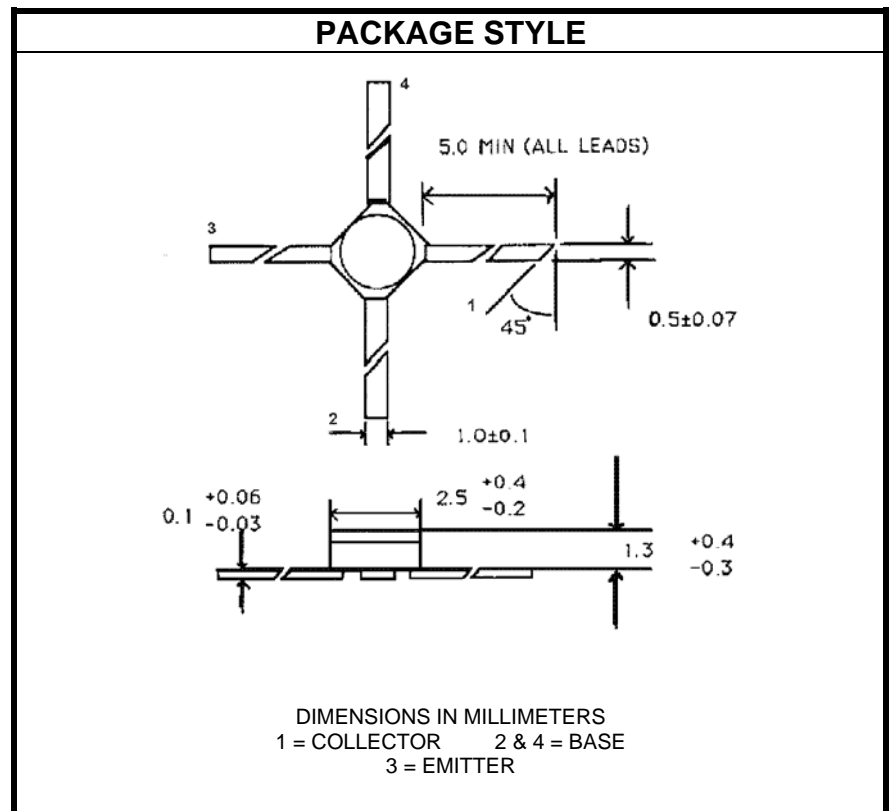
NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **HXTR4101** is a Common Base Device Designed for Oscillator Applications up to 10 GHz.

MAXIMUM RATINGS

| | |
|------------------------|---------------------------------|
| I_C | 70 mA |
| V_{EB0} | 1.5 V |
| V_{CEO} | 20 V |
| T_J | 300 °C |
| T_{STG} | -65 °C to 250 °C |
| P_T | 900 mW @ T _C = 25 °C |


CHARACTERISTICS T_C = 25 °C

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|------------------------|--|---------|---------|---------|--------|
| I_{CEO} | V _{CE} = 15 V | | | 500 | nA |
| I_{CBO} | V _{CB} = 15 V | | | 100 | nA |
| h_{FE} | V _{CE} = 15 V I _C = 15 mA | 50 | 120 | 220 | --- |
| P_{osc} | V _{CB} = 15 V I _C = 30mA f = 3.0 GHz | | 21.5 | | dBm |
| | I _C = 30 mA f = 4.3 GHz | 19 | 20.5 | | |
| | I _C = 30 mA f = 6.0 GHz | | 17 | | |
| | I _C = 30 mA f = 8.0 GHz | | 12 | | |
| N/C | PHASE NOISE TO CARRIER @ 1.0 KHz FROM THE CARRIER(SSB) f = 4.3 GHz | | -50 | | dBc/Hz |